

# Michael Kneissl

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

351  
papers

8,555  
citations

43  
h-index

78  
g-index

394  
ext. papers

9,743  
ext. citations

2.7  
avg, IF

5.99  
L-index

#	Paper	IF	Citations
351	Impact of operation parameters on the degradation of 233 nm AlGaIn-based far-UVC LEDs. <i>Journal of Applied Physics</i> , <b>2022</b> , 131, 014501	2.5	5
350	Application of 233nm far-UVC LEDs for eradication of MRSA and MSSA and risk assessment on skin models.. <i>Scientific Reports</i> , <b>2022</b> , 12, 2587	4.9	5
349	The influence of threading dislocations propagating through an AlGaIn UVC LED. <i>Applied Physics Letters</i> , <b>2022</b> , 120, 162101	3.4	1
348	Origin of defect luminescence in ultraviolet emitting AlGaIn diode structures. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 202101	3.4	1
347	Electrical and optical characteristics of highly transparent MOVPE-grown AlGaIn-based tunnel heterojunction LEDs emitting at 232 nm. <i>Photonics Research</i> , <b>2021</b> , 9, 1117	6	4
346	Light extraction efficiency and internal quantum efficiency of fully UVC-transparent AlGaIn based LEDs. <i>Journal Physics D: Applied Physics</i> , <b>2021</b> , 54, 335101	3	6
345	A 310 nm Optically Pumped AlGaIn Vertical-Cavity Surface-Emitting Laser. <i>ACS Photonics</i> , <b>2021</b> , 8, 135-143	3	7
344	Influence of the hydrogen level in (InAlGa)N-based laser diodes on the stability of the device's operating voltage. <i>Journal Physics D: Applied Physics</i> , <b>2021</b> , 54, 135103	3	0
343	Skin tolerant inactivation of multiresistant pathogens using far-UVC LEDs. <i>Scientific Reports</i> , <b>2021</b> , 11, 14647	4.9	9
342	Quantification of Trace-Level Silicon Doping in Al GaIn Films Using Wavelength-Dispersive X-Ray Microanalysis. <i>Microscopy and Microanalysis</i> , <b>2021</b> , 27, 696-704	0.5	1
341	Effect of Inhomogeneous Broadening in Ultraviolet III-Nitride Light-Emitting Diodes.. <i>Materials</i> , <b>2021</b> , 14,	3.5	1
340	Reliability of UVC LEDs fabricated on AlN/sapphire templates with different threading dislocation densities. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 241104	3.4	15
339	Vertical conductivity and Poole-Frenkel-ionization of Mg acceptors in AlGaIn short-period superlattices with high Al mole fraction. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 252101	3.4	7
338	Low resistance n-contact for UVC LEDs by a two-step plasma etching process. <i>Semiconductor Science and Technology</i> , <b>2020</b> , 35, 095019	1.8	2
337	Enhanced Wall Plug Efficiency of AlGaIn-Based Deep-UV LEDs Using Mo/Al as p-Contact. <i>IEEE Photonics Technology Letters</i> , <b>2020</b> , 1-1	2.2	4
336	Thin-film flip-chip UVB LEDs realized by electrochemical etching. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 121101	3.4	5
335	Status and Prospects of AlN Templates on Sapphire for Ultraviolet Light-Emitting Diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2020</b> , 217, 1901022	1.6	18

334	Polarization fields in semipolar (202 × 1 ×) and (202 × 1) InGaN light emitting diodes. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 062106	3.4	
333	Structural and luminescence imaging and characterisation of semiconductors in the scanning electron microscope. <i>Semiconductor Science and Technology</i> , <b>2020</b> , 35, 054001	1.8	3
332	Continuous-wave operation of DFB laser diodes based on GaN using 10 <sup>th</sup> -order laterally coupled surface gratings. <i>Optics Letters</i> , <b>2020</b> , 45, 935-938	3	7
331	Improved performance of UVC-LEDs by combination of high-temperature annealing and epitaxially laterally overgrown AlN/sapphire. <i>Photonics Research</i> , <b>2020</b> , 8, 589	6	26
330	Electrical properties and microstructure formation of V/Al-based n-contacts on high Al mole fraction n-AlGaIn layers. <i>Photonics Research</i> , <b>2020</b> , 8, 1381	6	15
329	A Short Introduction to Semiconductor Nanophotonics. <i>Springer Series in Solid-state Sciences</i> , <b>2020</b> , 1-11	0.4	0
328	Group III-Nitride-Based UV Laser Diodes. <i>Springer Series in Solid-state Sciences</i> , <b>2020</b> , 505-548	0.4	1
327	Effect of unevenly-distributed V pits on the optical and electrical characteristics of green micro-light emitting diode. <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 045106	3	3
326	AlN overgrowth of nano-pillar-patterned sapphire with different offcut angle by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , <b>2020</b> , 531, 125343	1.6	10
325	Improving AlN Crystal Quality and Strain Management on Nanopatterned Sapphire Substrates by High-Temperature Annealing for UVC Light-Emitting Diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2020</b> , 217, 1900796	1.6	12
324	Improvement in the Reliability of AlGaInP-Based Light-Emitting Diode Package Using Optimal Silicon and Leadframe Structure. <i>ECS Journal of Solid State Science and Technology</i> , <b>2020</b> , 9, 015014	2	3
323	The 2020 UV emitter roadmap. <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 503001	3	123
322	Electrical properties of (11-22) Si:AlGaIn layers at high Al contents grown by metal-organic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 221101	3.4	6
321	Electrical compensation and cation vacancies in Al rich Si-doped AlGaIn. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 142103	3.4	5
320	Milliwatt power 233 nm AlGaIn-based deep UV-LEDs on sapphire substrates. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 111102	3.4	21
319	Calculation of optical gain in AlGaIn quantum wells for ultraviolet emission. <i>AIP Advances</i> , <b>2020</b> , 10, 095303	3	7
318	Advances in electron channelling contrast imaging and electron backscatter diffraction for imaging and analysis of structural defects in the scanning electron microscope. <i>IOP Conference Series: Materials Science and Engineering</i> , <b>2020</b> , 891, 012023	0.4	
317	Electrochemical etching of AlGaIn for the realization of thin-film devices. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 182103	3.4	8

316	High-Current Stress of UV-B (In)AlGa <sub>N</sub> -Based LEDs: Defect-Generation and Diffusion Processes. <i>IEEE Transactions on Electron Devices</i> , <b>2019</b> , 66, 3387-3392	2.9	13
315	Optical light polarization and light extraction efficiency of AlGa <sub>N</sub> -based LEDs emitting between 264 and 220 nm. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SCCB20	1.4	21
314	Influence of InN and AlN concentration on the compositional inhomogeneity and formation of InN-rich regions in In <sub>x</sub> Al <sub>y</sub> Ga <sub>1-x-y</sub> N. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SCCB18	1.4	2
313	Indium incorporation in quaternary In <sub>x</sub> Al <sub>y</sub> Ga <sub>1-x-y</sub> N for UVB-LEDs. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SC1004	1.4	5
312	Precise determination of polarization fields in c-plane GaN/Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterostructures with capacitance-voltage-measurements. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SCCB08	1.4	2
311	Degradation of (In)AlGa <sub>N</sub> -Based UVB LEDs and Migration of Hydrogen. <i>IEEE Photonics Technology Letters</i> , <b>2019</b> , 31, 529-532	2.2	29
310	The emergence and prospects of deep-ultraviolet light-emitting diode technologies. <i>Nature Photonics</i> , <b>2019</b> , 13, 233-244	33.9	458
309	Reducing the grain density in semipolar (11-22) AlGa <sub>N</sub> surfaces on m-plane sapphire substrates. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SC1026	1.4	2
308	Effect of quantum barrier composition on electro-optical properties of AlGa <sub>N</sub> -based UVC light emitting diodes. <i>Semiconductor Science and Technology</i> , <b>2019</b> , 34, 085007	1.8	6
307	Influence of substrate off-cut angle on the performance of 310 nm light emitting diodes. <i>Journal of Crystal Growth</i> , <b>2019</b> , 526, 125241	1.6	7
306	Determination of Sapphire Off-Cut and Its Influence on the Morphology and Local Defect Distribution in Epitaxially Laterally Overgrown AlN for Optically Pumped UVC Lasers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2019</b> , 216, 1900682	1.6	7
305	Hole injection mechanism in the quantum wells of blue light emitting diode with V pits for micro-display application. <i>Applied Physics Express</i> , <b>2019</b> , 12, 102016	2.4	5
304	Inhomogeneous spectral broadening in deep ultraviolet light emitting diodes <b>2019</b> ,		3
303	MOVPE-grown AlGa <sub>N</sub> -based tunnel heterojunctions enabling fully transparent UVC LEDs. <i>Photonics Research</i> , <b>2019</b> , 7, B7	6	34
302	Current-induced degradation and lifetime prediction of 310 nm ultraviolet light-emitting diodes. <i>Photonics Research</i> , <b>2019</b> , 7, B36	6	27
301	Scanning electron microscopy as a flexible technique for investigating the properties of UV-emitting nitride semiconductor thin films. <i>Photonics Research</i> , <b>2019</b> , 7, B73	6	6
300	Displacement Talbot lithography for nano-engineering of III-nitride materials. <i>Microsystems and Nanoengineering</i> , <b>2019</b> , 5, 52	7.7	19
299	Influence of light absorption on the performance characteristics of UV LEDs with emission between 239 and 217 nm. <i>Applied Physics Express</i> , <b>2019</b> , 12, 012008	2.4	26

298	On the optical polarization properties of semipolar (202°1) and (202°1°) InGaN/GaN quantum wells. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 085705	2.5	6
297	DFB Laser Diodes Based on GaN Using 10th Order Laterally Coupled Surface Gratings. <i>IEEE Photonics Technology Letters</i> , <b>2018</b> , 30, 231-234	2.2	23
296	AlGaIn-based deep UV LEDs grown on sputtered and high temperature annealed AlN/sapphire. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 041110	3.4	136
295	Influence of template properties and quantum well number on stimulated emission from Al <sub>0.7</sub> Ga <sub>0.3</sub> N/Al <sub>0.8</sub> Ga <sub>0.2</sub> N quantum wells. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 035015	1.8	3
294	MOVPE Growth of Smooth and Homogeneous Al <sub>0.8</sub> Ga <sub>0.2</sub> N:Si Superlattices as UVC Laser Cladding Layers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2018</b> , 215, 1800005	1.6	7
293	Degradation effects of the active region in UV-C light-emitting diodes. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 104502	2.5	35
292	Effect of the GaN:Mg Contact Layer on the Light-Output and Current-Voltage Characteristic of UVB LEDs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2018</b> , 215, 1700643	1.6	13
291	Auger recombination in AlGaIn quantum wells for UV light-emitting diodes. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 071107	3.4	41
290	Influence of waveguide strain and surface morphology on AlGaIn-based deep UV laser characteristics. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 415101	3	11
289	Degradation behavior of AlGaIn-based 233 nm deep-ultraviolet light emitting diodes. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 095017	1.8	13
288	10th order laterally coupled GaN-based DFB laser diodes with V-shaped surface gratings <b>2018</b> ,		3
287	Defect-generation and diffusion in (In)AlGaIn-based UV-B LEDs submitted to constant current stress <b>2018</b> ,		2
286	Bow Reduction of AlInGaIn-Based Deep UV LED Wafers Using Focused Laser Patterning. <i>IEEE Photonics Technology Letters</i> , <b>2018</b> , 30, 1792-1794	2.2	1
285	Accurate determination of polarization fields in (0001) c-plane InAlN/GaN heterostructures with capacitance-voltage-measurements. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 485103	3	3
284	Localization of current-induced degradation effects in (InAlGa)N-based UV-B LEDs. <i>Journal of Applied Physics</i> , <b>2018</b> , 124, 084504	2.5	16
283	Metamorphic Al <sub>0.5</sub> Ga <sub>0.5</sub> N:Si on AlN/sapphire for the growth of UVB LEDs. <i>Journal of Crystal Growth</i> , <b>2017</b> , 464, 185-189	1.6	33
282	Analysis of doping concentration and composition in wide bandgap AlGaIn:Si by wavelength dispersive x-ray spectroscopy. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 035020	1.8	13
281	The effects of magnesium doping on the modal loss in AlGaIn-based deep UV lasers. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 081103	3.4	25

280	Improved light extraction and quantum efficiencies for UVB LEDs with UV-transparent p-AlGaIn superlattices (Conference Presentation) <b>2017</b> ,		4
279	Surface reconstructions of (0001) AlN during metal-organic vapor phase epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , <b>2017</b> , 254, 1600711	1.3	5
278	Growth and Optical Properties of GaN-Based Non- and Semipolar LEDs. <i>Topics in Applied Physics</i> , <b>2017</b> , 93-128	0.5	1
277	Defect generation in deep-UV AlGaIn-based LEDs investigated by electrical and spectroscopic characterisation <b>2017</b> ,		3
276	Design considerations for AlGaIn-based UV LEDs emitting near 235 nm with uniform emission pattern. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 045019	1.8	4
275	Optically Pumped DFB Lasers Based on GaN Using 10th-Order Laterally Coupled Surface Gratings. <i>IEEE Photonics Technology Letters</i> , <b>2017</b> , 29, 138-141	2.2	12
274	. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 200-205	2.9	41
273	Effect of Cl <sub>2</sub> plasma treatment and annealing on vanadium based metal contacts to Si-doped Al <sub>0.75</sub> Ga <sub>0.25</sub> N. <i>Journal of Applied Physics</i> , <b>2017</b> , 122, 125701	2.5	8
272	Effect of Electron Blocking Layer Doping and Composition on the Performance of 310 nm Light Emitting Diodes. <i>Materials</i> , <b>2017</b> , 10,	3.5	15
271	Controlling the morphology transition between step-flow growth and step-bunching growth. <i>Journal of Crystal Growth</i> , <b>2017</b> , 478, 187-192	1.6	30
270	Chip design for thin-film deep ultraviolet LEDs fabricated by laser lift-off of the sapphire substrate. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 12LT01	1.8	11
269	Gas Sensing of Nitrogen Oxide Utilizing Spectrally Pure Deep UV LEDs. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2017</b> , 23, 29-36	3.8	32
268	Highly Reflective p-Contacts Made of Pd-Al on Deep Ultraviolet Light-Emitting Diodes. <i>IEEE Photonics Technology Letters</i> , <b>2017</b> , 29, 2222-2225	2.2	8
267	Recombination mechanisms and thermal droop in AlGaIn-based UV-B LEDs. <i>Photonics Research</i> , <b>2017</b> , 5, A44	6	24
266	A Miniaturized UV-LED Based Optical Gas Sensor Utilizing Silica Waveguides for the Measurement of Nitrogen Dioxide and Sulphur Dioxide. <i>Proceedings (mdpi)</i> , <b>2017</b> , 1, 556	0.3	2
265	Impact of inhomogeneous broadening on optical polarization of high-inclination semipolar and nonpolar In <sub>x</sub> Ga <sub>1-x</sub> N/GaN quantum wells. <i>Physical Review B</i> , <b>2016</b> , 93,	3.3	20
264	Impact of acceptor concentration on the resistivity of Ni/Au p-contacts on semipolar (2001) GaN:Mg. <i>Physica Status Solidi (B): Basic Research</i> , <b>2016</b> , 253, 169-173	1.3	8
263	On optical polarization and charge carrier statistics of nonpolar InGaIn quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , <b>2016</b> , 253, 145-157	1.3	6

262	Influence of the LED heterostructure on the degradation behavior of (InAlGa)N-based UV-B LEDs <b>2016</b> ,		1
261	Preparation and structure of ultra-thin GaN (0001) layers on In <sub>0.11</sub> Ga <sub>0.89</sub> N-single quantum wells. <i>Materials Science in Semiconductor Processing</i> , <b>2016</b> , 55, 7-11	4.3	12
260	A Brief Review of III-Nitride UV Emitter Technologies and Their Applications. <i>Springer Series in Materials Science</i> , <b>2016</b> , 1-25	0.9	46
259	Correlation of sapphire off-cut and reduction of defect density in MOVPE grown AlN. <i>Physica Status Solidi (B): Basic Research</i> , <b>2016</b> , 253, 809-813	1.3	29
258	Low absorption loss p-AlGaIn superlattice cladding layer for current-injection deep ultraviolet laser diodes. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 151108	3.4	39
257	On the formation of cleaved mirror facets of GaN-based laser diodes—A comparative study of diamond-tip edge-scribing and laser scribing. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2016</b> , 34, 041222	1.3	4
256	Electronic properties of Si-doped Al <sub>x</sub> Ga <sub>1-x</sub> N with aluminum mole fractions above 80%. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 145702	2.5	34
255	Dominance of radiative recombination from electron-beam-pumped deep-UV AlGaIn multi-quantum-well heterostructures. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 181105	3.4	28
254	Determination of polarization fields in group III-nitride heterostructures by capacitance-voltage-measurements. <i>Journal of Applied Physics</i> , <b>2016</b> , 119, 095713	2.5	8
253	Role of substrate quality on the performance of semipolar (112̄) InGaIn light-emitting diodes. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 135701	2.5	7
252	Surface properties of AlInGaIn/GaN heterostructure. <i>Materials Science in Semiconductor Processing</i> , <b>2016</b> , 55, 26-31	4.3	7
251	MOVPE growth and indium incorporation of polar, semipolar (112) and (201) InGaIn. <i>Physica Status Solidi (B): Basic Research</i> , <b>2016</b> , 253, 93-98	1.3	4
250	Embedded GaIn nanostripes on c-sapphire for DFB lasers with semipolar quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , <b>2016</b> , 253, 180-185	1.3	5
249	Efficient carrier-injection and electron-confinement in UV-B light-emitting diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2016</b> , 213, 210-214	1.6	18
248	Index-Antiguinding in Narrow-Ridge GaIn-Based Laser Diodes Investigated by Measurements of the Current-Dependent Gain and Index Spectra and by Self-Consistent Simulation. <i>IEEE Journal of Quantum Electronics</i> , <b>2015</b> , 51, 1-6	2	4
247	Current spreading in UV-C LEDs emitting at 235 nm <b>2015</b> ,		1
246	Effect of heterostructure design on carrier injection and emission characteristics of 295 nm light emitting diodes. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 195704	2.5	28
245	Anisotropic optical properties of semipolar AlGaIn layers grown on m-plane sapphire. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 182102	3.4	14

244	High-power UV-B LEDs with long lifetime <b>2015</b> ,		38
243	UV-C Lasing From AlGa <sub>N</sub> Multiple Quantum Wells on Different Types of AlN/Sapphire Templates. <i>IEEE Photonics Technology Letters</i> , <b>2015</b> , 27, 1969-1972	2.2	18
242	MOVPE growth of semipolar (112̄) Al <sub>1-x</sub> In <sub>x</sub> N across the alloy composition range (0̄0.55). <i>Journal of Crystal Growth</i> , <b>2015</b> , 411, 106-109	1.6	15
241	V-pit to truncated pyramid transition in AlGa <sub>N</sub> -based heterostructures. <i>Semiconductor Science and Technology</i> , <b>2015</b> , 30, 114010	1.8	17
240	Temperature induced degradation of InAlGa <sub>N</sub> multiple-quantum well UV-B LEDs. <i>Materials Research Society Symposia Proceedings</i> , <b>2015</b> , 1792, 1		6
239	Spatial clustering of defect luminescence centers in Si-doped low resistivity Al <sub>0.82</sub> Ga <sub>0.18</sub> N. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 072103	3.4	20
238	Degradation of (InAlGa) <sub>N</sub> -based UV-B light emitting diodes stressed by current and temperature. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 094504	2.5	35
237	Strongly transverse-electric-polarized emission from deep ultraviolet AlGa <sub>N</sub> quantum well light emitting diodes. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 142101	3.4	63
236	Spatial inhomogeneities in Al <sub>x</sub> Ga <sub>1-x</sub> N quantum wells induced by the surface morphology of AlN/sapphire templates. <i>Semiconductor Science and Technology</i> , <b>2015</b> , 30, 114008	1.8	11
235	In-situ observation of InGa <sub>N</sub> quantum well decomposition during growth of laser diodes. <i>Crystal Research and Technology</i> , <b>2015</b> , 50, 499-503	1.3	7
234	Desorption induced Ga <sub>N</sub> quantum dots on (0001) AlN by MOVPE. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2015</b> , 9, 526-529	2.5	7
233	Quality CuInSe <sub>2</sub> and Cu(In,Ga)Se <sub>2</sub> thin films processed by single-step electrochemical deposition techniques. <i>Materials Research Express</i> , <b>2015</b> , 2, 056402	1.7	5
232	Challenges for AlGa <sub>N</sub> Based UV Laser Diodes <b>2015</b> ,		3
231	Influence of barrier growth schemes on the structural properties and thresholds of InGa <sub>N</sub> quantum well laser diodes. <i>Journal of Crystal Growth</i> , <b>2014</b> , 391, 46-51	1.6	12
230	Surface topology caused by dislocations in polar, semipolar, and nonpolar InGa <sub>N</sub> /Ga <sub>N</sub> heterostructures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2014</b> , 211, 756-760	1.6	4
229	Nano-optical analysis of Ga <sub>N</sub> -based diode lasers. <i>Semiconductor Science and Technology</i> , <b>2014</b> , 29, 112001.8		3
228	Performance Characteristics of UV-C AlGa <sub>N</sub> -Based Lasers Grown on Sapphire and Bulk AlN Substrates. <i>IEEE Photonics Technology Letters</i> , <b>2014</b> , 26, 342-345	2.2	92
227	Analysis of crystal orientation in AlN layers grown on m-plane sapphire. <i>Journal of Crystal Growth</i> , <b>2014</b> , 400, 54-60	1.6	14



226	Surface and crystal structure of nitridated sapphire substrates and their effect on polar InN layers. <i>Applied Surface Science</i> , <b>2014</b> , 307, 461-467	6.7	10
225	Multicharacterization approach for studying InAl(GaN)/Al(GaN)/GaN heterostructures for high electron mobility transistors. <i>AIP Advances</i> , <b>2014</b> , 4, 127101	1.5	13
224	Low-threshold stimulated emission at 249 nm and 256 nm from AlGaIn-based multiple-quantum-well lasers grown on sapphire substrates. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 141106	3.4	68
223	Effect of quantum well non-uniformities on lasing threshold, linewidth, and lateral near field filamentation in violet (Al,In)GaN laser diodes. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 173501	3.4	7
222	Impact of electron irradiation on electron holographic potentiometry. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 094102	3.4	23
221	Efficient charge carrier injection into sub-250 nm AlGaIn multiple quantum well light emitting diodes. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 051113	3.4	83
220	Polarization of photoluminescence emission from semi-polar (11 $\bar{2}$ ) AlGaIn layers. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 051906	3.4	7
219	Growth and Optical Properties of GaN-Based Non- and Semipolar LEDs. <i>Topics in Applied Physics</i> , <b>2013</b> , 83-119	0.5	3
218	Investigation of the temperature dependent efficiency droop in UV LEDs. <i>Semiconductor Science and Technology</i> , <b>2013</b> , 28, 125021	1.8	11
217	Controlled coalescence of MOVPE grown AlN during lateral overgrowth. <i>Journal of Crystal Growth</i> , <b>2013</b> , 368, 83-86	1.6	31
216	Determination of lattice parameters, strain state and composition in semipolar III-nitrides using high resolution X-ray diffraction. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 213509	2.5	26
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201	Surface Transitions During InGa <sub>N</sub> Growth on GaN(0001) in Metal-Organic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 08JB23	1.4	5
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